

AZ100LVEL16VR



PECL/ECL Oscillator Gain Stage & Buffer with Selectable Enable

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FEATURES

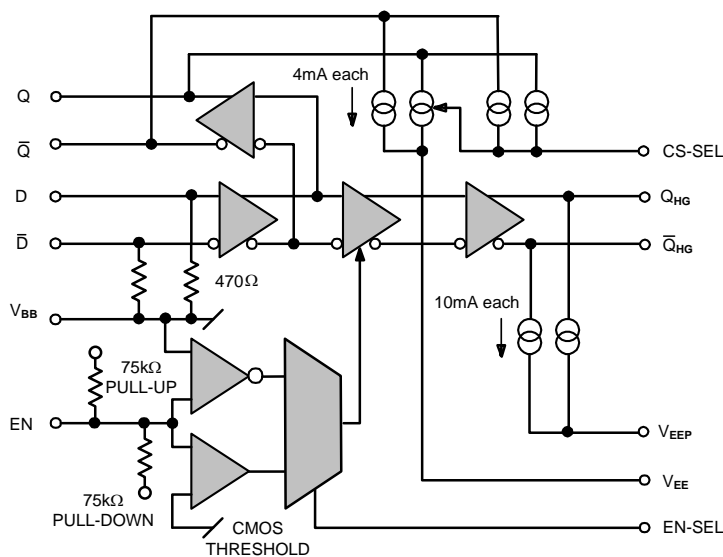
- Minimizes External Components
- Selectable Enable Polarity and Threshold (CMOS or PECL)
- High Bandwidth for $\geq 1\text{GHz}$
- Similar operation as AZ100EL16VO
- -147 dBc/Hz Typical Noise Floor

DESCRIPTION

The AZ100LVEL16VR is a specialized oscillator gain stage with a high gain output buffer including an enable function. The Q_{HG}/\bar{Q}_{HG} outputs have voltage gain several times greater than the Q/Q outputs. It provides a selectable Q_{HG}/\bar{Q}_{HG} enable that allows continuous oscillator operation via the Q/Q outputs.

The AZ100LVEL16VR provides adjustable internal pull-down current sources for the Q/Q outputs and optional 10mA current sources for the Q_{HG}/\bar{Q}_{HG} outputs. Internal input biasing further reduces the number of needed external components

BLOCK DIAGRAM



APPLICATIONS

- Crystal or saw oscillators that require minimal external components.

PACKAGE AVAILABILITY

- MLP8
 - Green/RoHS Compliant/Pb-Free
- MLP16
 - Green/RoHS Compliant/Pb-Free

Order Number	Package	Marking
AZ100LVEL16VRLG ¹	MLP16	100G / 16R / <Date Code> ²
AZ100LVEL16VRNEG ¹	MLP8	R5G / <Date Code> ²

¹ Tape & Reel - Add 'R1' at end of order number for 7in (1k parts), 'R2' (2.5k) for 13in

² See www.azmicrotek.com for date code format

PIN DESCRIPTION AND CONFIGURATION

Table 1 - Pin Description AZ100LVEL16VRL

Pin	Name	Type	Function
1	NC	-	N/A
2	D	Input	Data Input
3	D	Input	Inverting Data Input
4	V _{BB}	Output	Reference Voltage
5	EN	Input	Output Enable
6	NC	-	N/A
7	V _{EE}	Power	Negative Supply
8	V _{EEP}	Input	High Gain Current Source Enable
9	EN-SEL	Input	Enable Polarity Select
10	Q _{HG}	Output	High Gain Inverting PECL Output
11	Q _{HG}	Output	High Gain PECL Output
12	CS-SEL	Input	Current Source Select
13	V _{CC}	Power	Positive Supply
14	NC	-	N/A
15	Q	Output	PECL Output
16	Q	Output	Inverting PECL Output

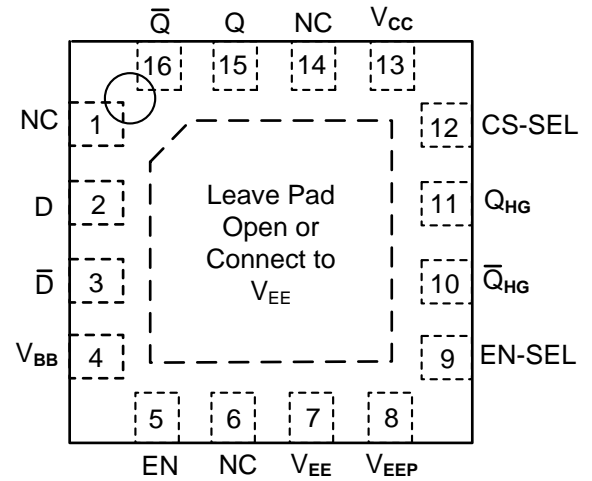


Figure 1 - Pin Configuration for AZ100LVEL16VRL

Table 2 - Pin Description AZ100LVEL16VRNEG

Pin	Name	Type	Function
1	D	Input	Data Input
2	V _{BB}	Output	Reference Voltage
3	EN	Input	Output Enable
4	V _{EE}	Power	Negative Supply
5	Q _{HG}	Output	High Gain Inverting PECL Output
6	Q _{HG}	Output	High Gain PECL Output
7	V _{CC}	Power	Positive Supply
8	Q	Output	Inverting PECL Output

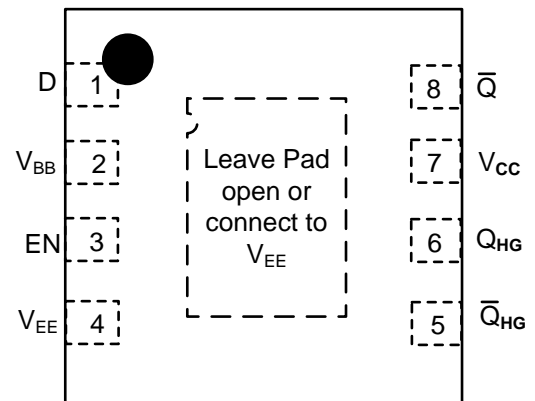


Figure 2 - Pin Configuration for AZ100LVEL16VRNEG

ENGINEERING NOTES**FUNCTIONALITY MLP16 PACKAGE (AZ100LVEL16VRL)**

The AZ100LVEL16VR provides a selectable Q_{HG}/\bar{Q}_{HG} enable that allows continuous oscillator operation via the Q/Q outputs. Table 3 shows the operating modes. Leaving EN-SEL open (NC) selects PECL/ECL operation for the EN pad/pin. In this mode the Q_{HG}/\bar{Q}_{HG} outputs are enabled when EN is left open (NC) or set to a PECL/ECL low.

Connecting EN-SEL to V_{CC} , V_{EE} or V_{BB} selects CMOS operation for the EN pad/pin. When EN-SEL is tied to V_{EE} , the Q_{HG}/\bar{Q}_{HG} outputs are disabled when EN is left open (NC). When EN-SEL is tied to V_{CC} or V_{BB} , the Q_{HG}/\bar{Q}_{HG} outputs are enabled when EN is left open. This default logic condition can be overridden by a $\leq 20k\Omega$ resistor connected to the opposite supply.

The AZ100LVEL16VR also provides a V_{BB} and 470Ω internal bias resistors from D to V_{BB} and \bar{D} to V_{BB} . The V_{BB} pin supports 1.5mA sink/source current. V_{BB} should be bypassed to ground or V_{CC} with a $0.01\ \mu\text{F}$ capacitor.

Outputs Q/Q each have a selectable on-chip pull-down current source. See Table 4 for the supported values. External resistors may also be used to increase pull-down current to a maximum total of 25mA for the Q/Q outputs.

Each of the Q_{HG}/\bar{Q}_{HG} outputs has an optional on-chip pull-down current source of 10mA. When pad/pin V_{EEP} is left open (NC), the output current sources are disabled and the Q_{HG}/\bar{Q}_{HG} operate as standard PECL/ECL. When V_{EEP} is connected to V_{EE} , the current sources are activated. The Q_{HG}/\bar{Q}_{HG} pull-down current can be decreased by using a resistor between V_{EEP} and V_{EE} .

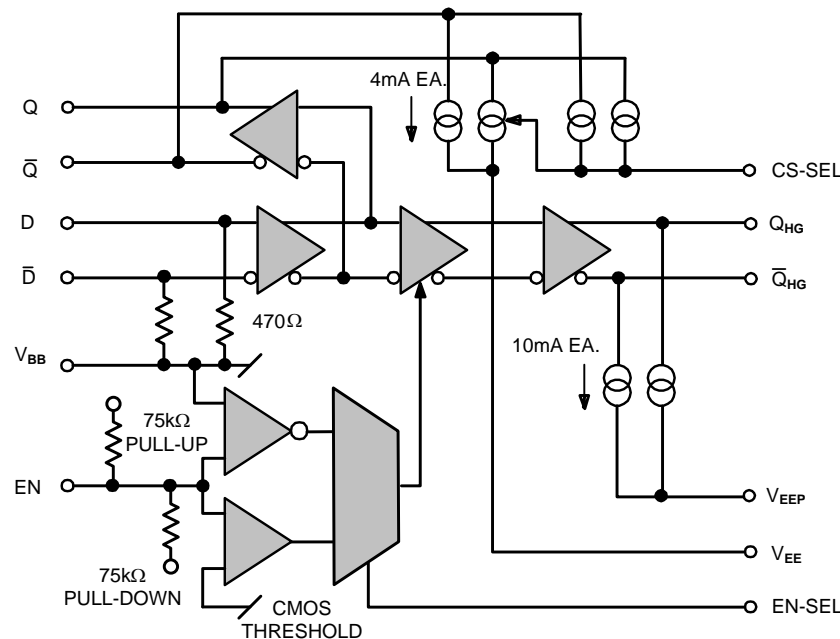


Figure 3 - AZ100LVEL16VRL Block Diagram

Table 3 – Enable Truth Table

EN-SEL	EN	Q/Q	Q _{HG}	Q _{HG}
NC	PECL Low, V _{EE} or NC	Data	Data	Data
	PECL High or V _{CC}	Data	Low	High
V _{EE} ¹	CMOS Low, V _{EE} or NC	Data	Low	High
	CMOS High or V _{CC}	Data	Data	Data
V _{CC} or V _{BB} ^{1,2}	CMOS Low or V _{EE}	Data	Low	High
	CMOS High, V _{CC} or NC	Data	Data	Data

¹ EN-SEL connections must be $\leq 1\Omega$.

² Date codes prior to 0428 do not support this operating mode.

Table 4 - Current Source Truth Table

CS-SEL	Q	Q
NC	4mA typ	4mA typ
V _{EE} ¹	8mA typ	8mA typ
V _{CC} ¹	0	4mA typ

1. Connection must be less than 1Ω

Figure 3 illustrates the timing sequences for the AZ100LVEL16VR in the MLP 16 package or as die. It is shown here with the enable operating in active Low mode with a PECL threshold. This mode is determined by leaving the EN-SEL open (NC). An active High enable with a CMOS/TTL threshold is also an option.

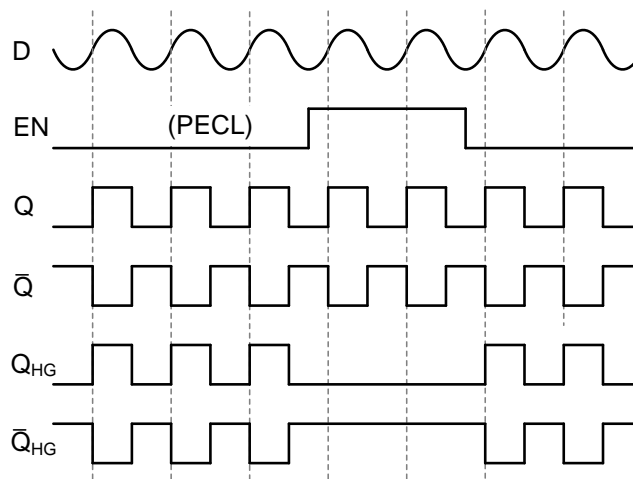


Figure 4 - AZ100LVEL16VRL Timing Diagram

FUNCTIONALITY MLP8 PACKAGE (AZ100LVEL16VRNEG)

A CMOS enable input (EN) allows continuous oscillator operation. When the EN input is HIGH or left open (NC), the Q and Q_{HG}/\bar{Q}_{HG} outputs follow the data input. When EN is LOW, the Q_{HG} output is forced high and the \bar{Q}_{HG} output is forced low while Q continues to follow the data input. The Q output has an internal 4 mA current source to V_{EE} , in most cases eliminating the need for an external pull-down resistor.

The AZ100LVEL16VRNEG also provides biasing. Data input D is tied to the V_{BB} pin through a 470Ω internal bias resistor while the inverting input \bar{D} is connected directly to V_{BB} . The V_{BB} pin supports 1.5mA sink/source current. V_{BB} should be bypassed to ground with a $0.01\ \mu\text{F}$ capacitor.

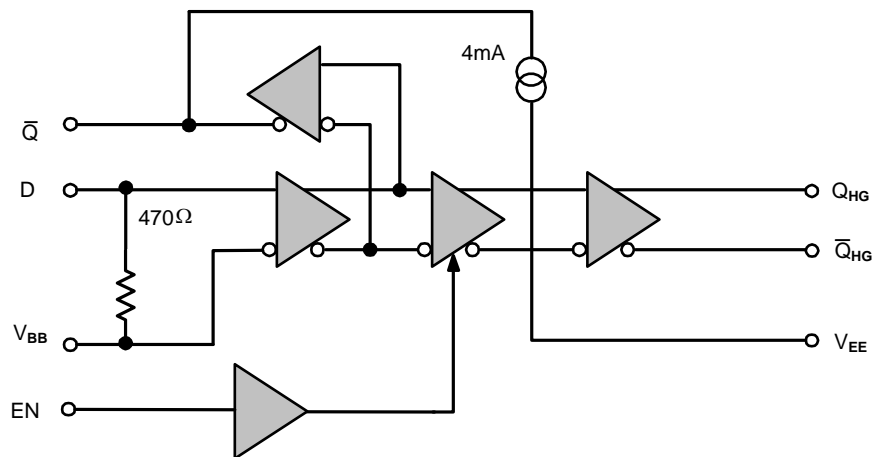


Figure 5 - AZ100LVEL16VRNEG Block Diagram

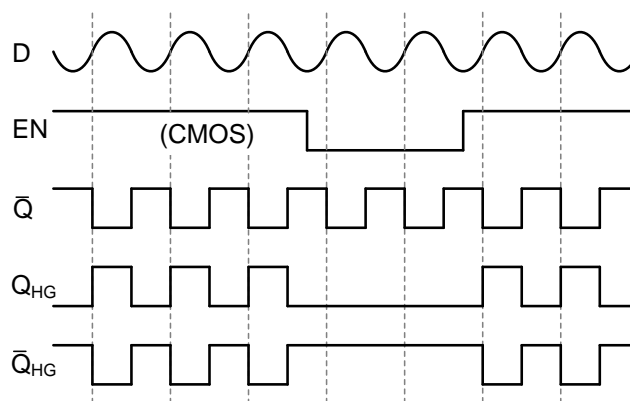


Figure 6 - AZ100LVEL16VRNEG Timing Diagram

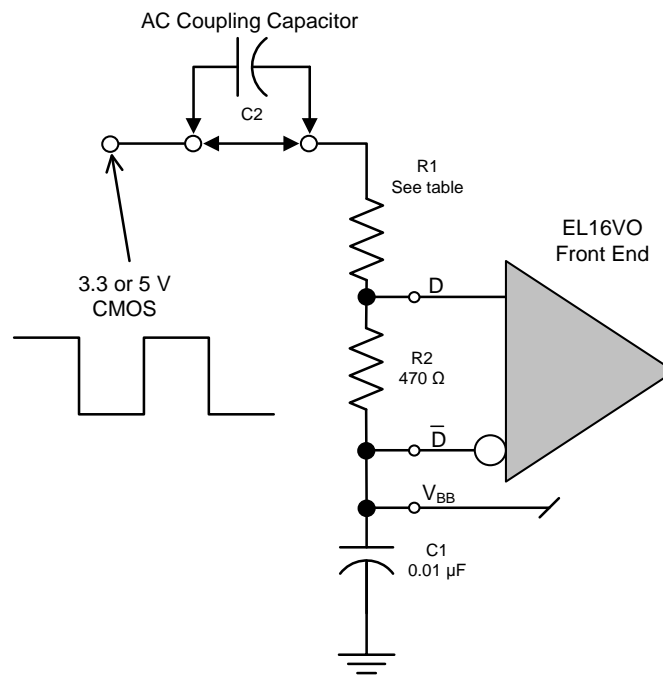
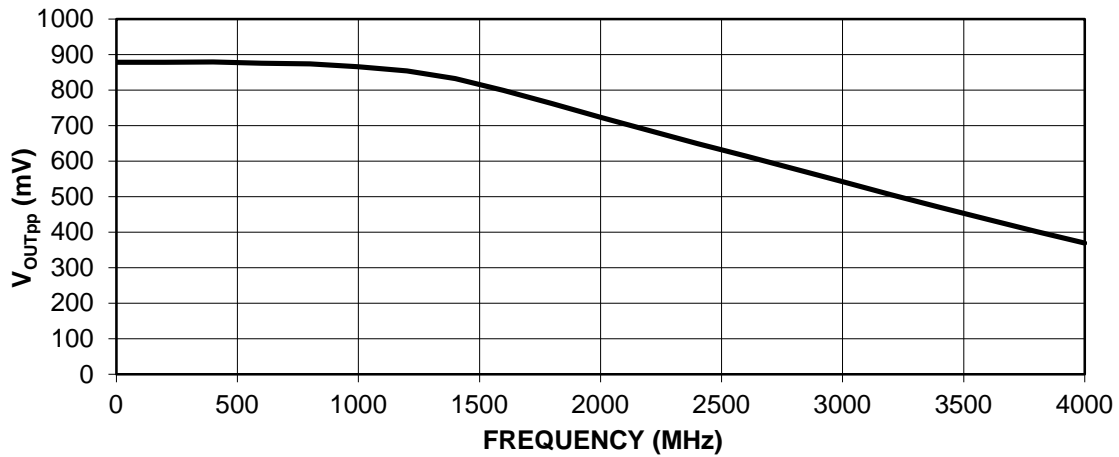


Figure 7 - Application Circuit for CMOS Inputs

Recommended Component Values for CMOS Single Ended Inputs

Input Type	R1 ¹ Value	
	AC Coupled (C2 in circuit)	DC Coupled (C2 shorted)
3.3 V CMOS	1.1 kΩ	2.0 kΩ
5.0 V CMOS	1.6 kΩ	3.3 kΩ

¹. R1 should be chosen so that the input swing on the D input with respect to D is in the range of ±80 to ±1000 mV, per the AC Characteristics table and the D input is < ±750 mV with respect to V_{BB}.

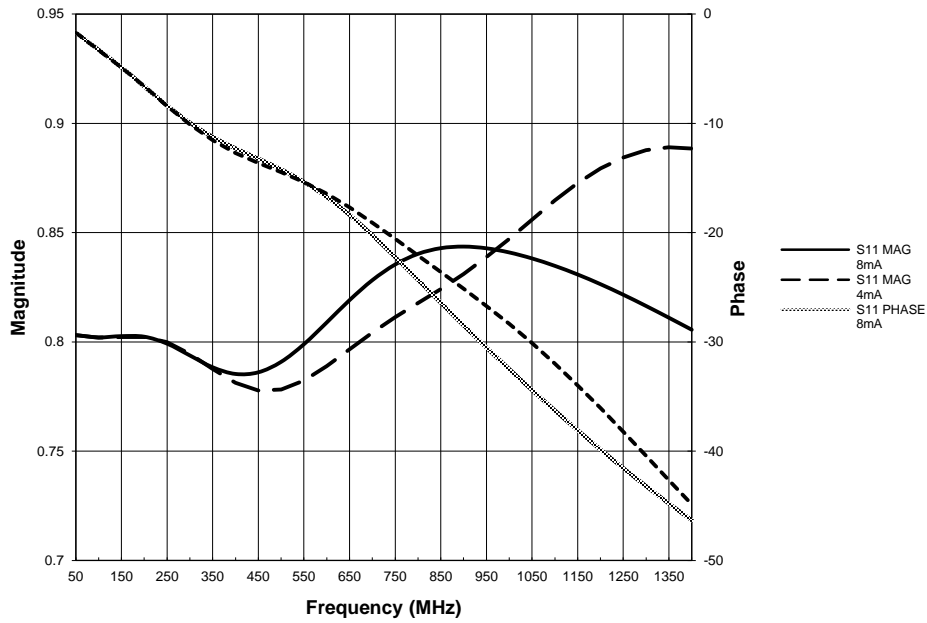


Figure 8 - S11 50Ω external AC, 4 & 8mA internal DC load

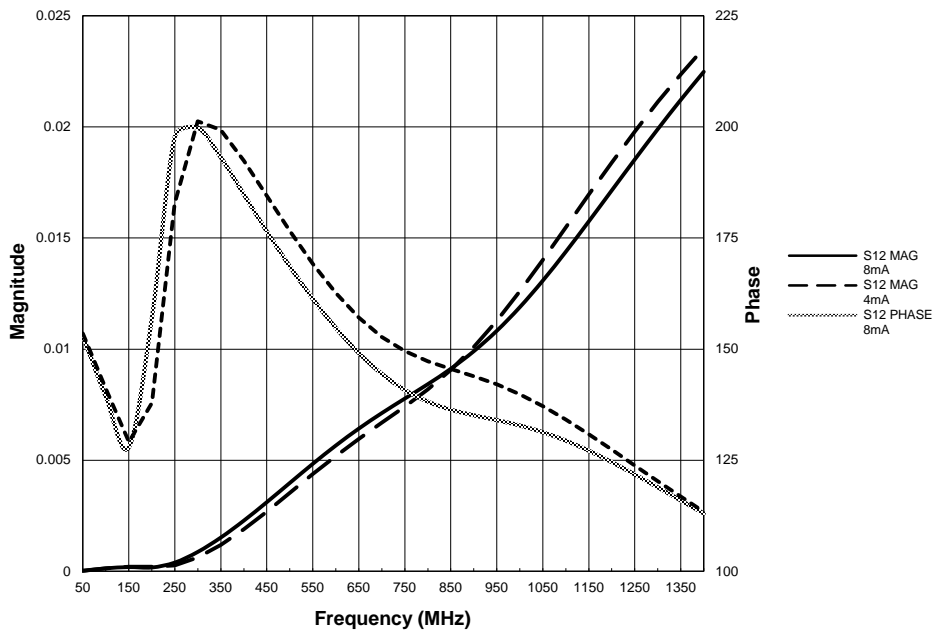


Figure 9 - S12 50Ω external AC, 4 & 8mA internal DC load

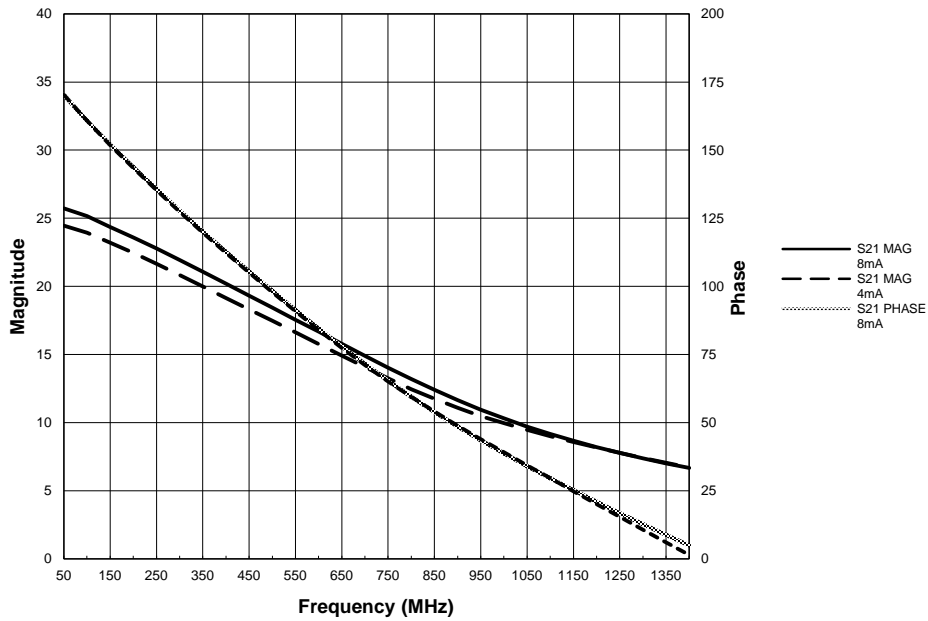


Figure 10 – S21 50Ω external AC, 4 & 8mA internal DC load

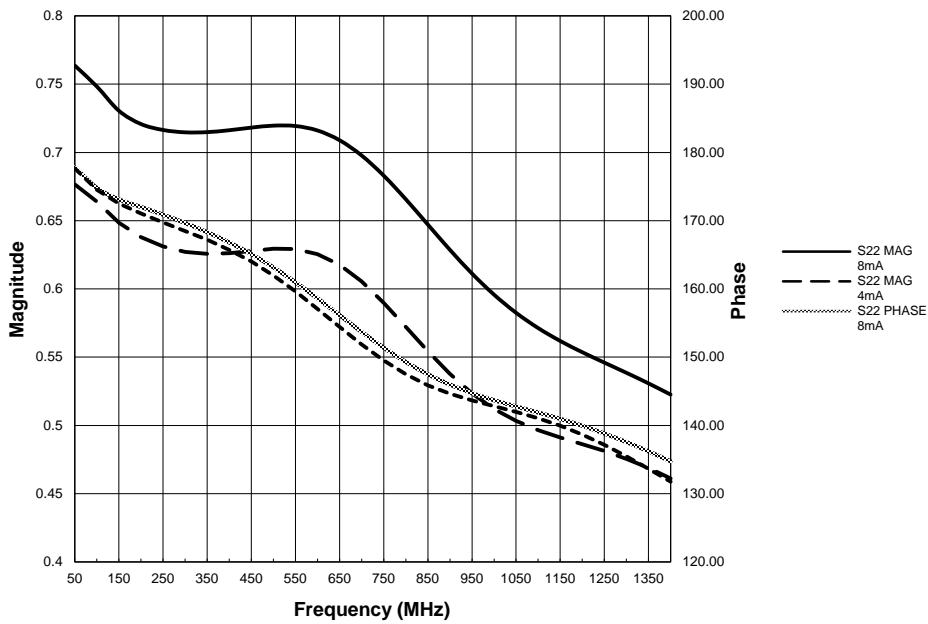


Figure 11 – S22 50Ω external AC, 4 & 8mA internal DC load

PERFORMANCE DATA

Table 5 – Absolute Maximum Ratings

Absolute Maximum Ratings are those values beyond which device life may be impaired.

Symbol	Characteristic	Condition	Rating	Unit
V _{CC}	PECL Power Supply	V _{EE} = 0V	0 to + 6.0	V
V _{D_PECL}	PECL D Input Voltage	Referenced to V _{BB}	±0.75	V
V _{EN_PECL}	PECL D Input Voltage	V _{EE} = 0V	0 to + 6.0	V
V _{EE}	ECL Power Supply	V _{CC} = 0V	-6.0 to 0	V
V _{D_ECL}	ECL D Input Voltage	Referenced to V _{BB}	±0.75	V
V _{EN_ECL}	ECL D Input Voltage	V _{CC} = 0V	-6.0 to 0	V
I _{OUT}	Output Current	Continuous Q	25	mA
		Surge Q	50	
		Continuous Q _{HG}	50	
		Surge Q _{HG}	100	
T _A	Operating Temperature Range	-	-40 to +85	°C
T _{STG}	Storage Temperature Range	-	-65 to +150	°C
ESD _{HBM}	Human Body Model Electro Static Discharge	-	2500	V
ESD _{MM}	Machine Model Electro Static Discharge	-	200	V
ESD _{CDM}	Charged Device Model Electro Static Discharge	-	2000	V

Table 6 - ECL DC Characteristics

ECL DC Characteristics (V_{EE} = -3.0V to -5.5V, V_{CC} = GND)

Symbol	Characteristic	-40°C		0°C		25°C		85°C		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
V _{OH}	Output HIGH Voltage ¹	-1045	-835	-1025	-835	-1025	-835	-1025	-835	mV
V _{OL}	Output LOW Voltage ¹	-1925	-1555	-1900	-1620	-1900	-1620	-1900	-1620	mV
V _{IH}	Input HIGH Voltage D,EN (ECL) ²	-1165	-740	-1165	-740	-1165	-740	-1165	-740	mV
	Input HIGH Voltage EN (CMOS) ³	V _{EE} + 2000	V _{CC}	V _{EE} + 2000	V _{CC}	V _{EE} + 2000	V _{CC}	V _{EE} + 2000	V _{CC}	mV
V _{IL}	Input LOW Voltage D,EN (ECL) ²	-1900	-1475	-1900	-1475	-1900	-1475	-1900	-1475	mV
	Input LOW Voltage EN (CMOS) ³	V _{EE}	V _{EE} + 800	V _{EE}	V _{EE} + 800	V _{EE}	V _{EE} + 800	V _{EE}	V _{EE} + 800	mV
V _{BB}	Reference Voltage	-1390	-1250	-1390	-1250	-1390	-1250	-1390	-1250	mV
I _{IH}	Input HIGH Current EN		150		150		150		150	μA
I _{IL}	Input LOW Current EN (ECL) ²	0.5		0.5		0.5		0.5		μA
	Input LOW Current EN (CMOS) ³	-150		-150		-150		-150		
I _{EE}	Power Supply Current ¹		48		48		48		54	mA

¹ Specified with each output terminated through 50Ω resistors to V_{CC} - 2V.² EN-SEL = NC³ EN-SEL = V_{CC} or V_{EE}

Table 7 - LVPECL DC Characteristics

LVPECL DC Characteristics ($V_{EE} = \text{GND}$, $V_{CC} = +3.3\text{V}$)

Symbol	Characteristic	-40°C		0°C		25°C		85°C		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
V_{OH}	Output HIGH Voltage ^{1,2}	2255	2465	2275	2465	2275	2465	2275	2465	mV
V_{OL}	Output LOW Voltage ^{1,2}	1375	1745	1400	1680	1400	1680	1400	1680	mV
V_{IH}	Input HIGH Voltage D,EN (ECL) ³	2135	2560	2135	2560	2135	2560	2135	2560	mV
	Input HIGH Voltage EN (CMOS) ⁴	2000	V_{CC}	2000	V_{CC}	2000	V_{CC}	2000	V_{CC}	mV
V_{IL}	Input LOW Voltage D,EN (ECL) ³	1400	1825	1400	1825	1400	1825	1400	1825	mV
	Input LOW Voltage EN (CMOS) ⁴	GND	800	GND	800	GND	800	GND	800	mV
V_{BB}	Reference Voltage ¹	1910	2050	1910	2050	1910	2050	1910	2050	mV
I_{IH}	Input HIGH Current EN		150		150		150		150	μA
I_{IL}	Input LOW Current EN (ECL) ³	0.5		0.5		0.5		0.5		μA
	Input LOW Current EN (CMOS) ⁴	-150		-150		-150		-150		
I_{EE}	Power Supply Current ²		48		48		48		54	mA

1 For supply voltages other than 3.3V, use the ECL table values and ADD supply voltage value

2 Specified with each output terminated through 50 Ω resistors to $V_{CC} - 2\text{V}$.

3 EN-SEL = NC

4 EN-SEL = V_{CC} or V_{EE}

Table 8 - PECL DC Characteristics

PECL DC Characteristics ($V_{EE} = \text{GND}$, $V_{CC} = +5.0\text{V}$)

Symbol	Characteristic	-40°C		0°C		25°C		85°C		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
V_{OH}	Output HIGH Voltage ^{1,2}	3955	4165	3975	4165	3975	4165	3975	4165	mV
V_{OL}	Output LOW Voltage ^{1,2}	3075	3445	3100	3380	3100	3380	3100	3380	mV
V_{IH}	Input HIGH Voltage D,EN (ECL) ³	3835	4260	3835	4260	3835	4260	3835	4260	mV
	Input HIGH Voltage EN (CMOS) ⁴	2000	V_{CC}	2000	V_{CC}	2000	V_{CC}	2000	V_{CC}	mV
V_{IL}	Input LOW Voltage D,EN (ECL) ³	3100	3525	3100	3525	3100	3525	3100	3525	mV
	Input LOW Voltage EN (CMOS) ⁴	GND	800	GND	800	GND	800	GND	800	mV
V_{BB}	Reference Voltage ¹	3610	3750	3610	3750	3610	3750	3610	3750	mV
I_{IH}	Input HIGH Current EN		150		150		150		150	μA
I_{IL}	Input LOW Current EN (ECL) ³	0.5		0.5		0.5		0.5		μA
	Input LOW Current EN (CMOS) ⁴	-150		-150		-150		-150		
I_{EE}	Power Supply Current ²		48		48		48		54	mA

1 For supply voltages other than 3.3V, use the ECL table values and ADD supply voltage value

2 Specified with each output terminated through 50 Ω resistors to $V_{CC} - 2\text{V}$.

3 EN-SEL = NC

4 EN-SEL = V_{CC} or V_{EE}

Table 9 - AC Characteristics

AC Characteristics ($V_{EE} = -3.0V$ to $-5.5V$; $V_{CC}=GND$ or $V_{EE}=GND$; $V_{CC} = +3.0V$ to $+5.5V$)

Symbol	Characteristic	-40°C			0°C			25°C			85°C			Unit
		Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	Min	Typ	Max	
t_{PLH}/t_{PHL}	Propagation Delay													
	D to Q ¹			400			400			400			400	ps
	D to Q _{HG} ¹			450			450			450			450	ps
t_{SKEW}	Duty Cycle Skew ³		5	20		5	20		5	20		5	20	ps
V_{PP} (AC)	Input Swing ⁴ Differential	80		1000	80		1000	80		1000	80		1000	mV
t_r/t_f	Output Rise/Fall ^{1,2} (20% - 80%)	100		240	100		240	100		240	100		240	ps

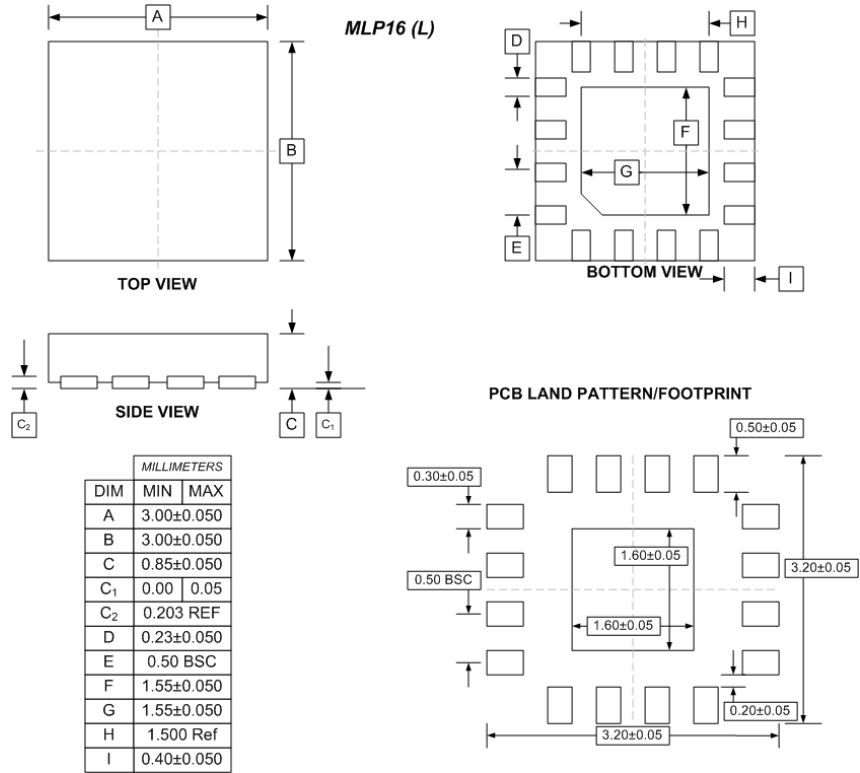
¹ Specified with CS-SEL connected to V_{EE} , Q terminated with an AC coupled to 50Ω load

² Specified with each output terminated through 50Ω resistors to $V_{CC} - 2V$.

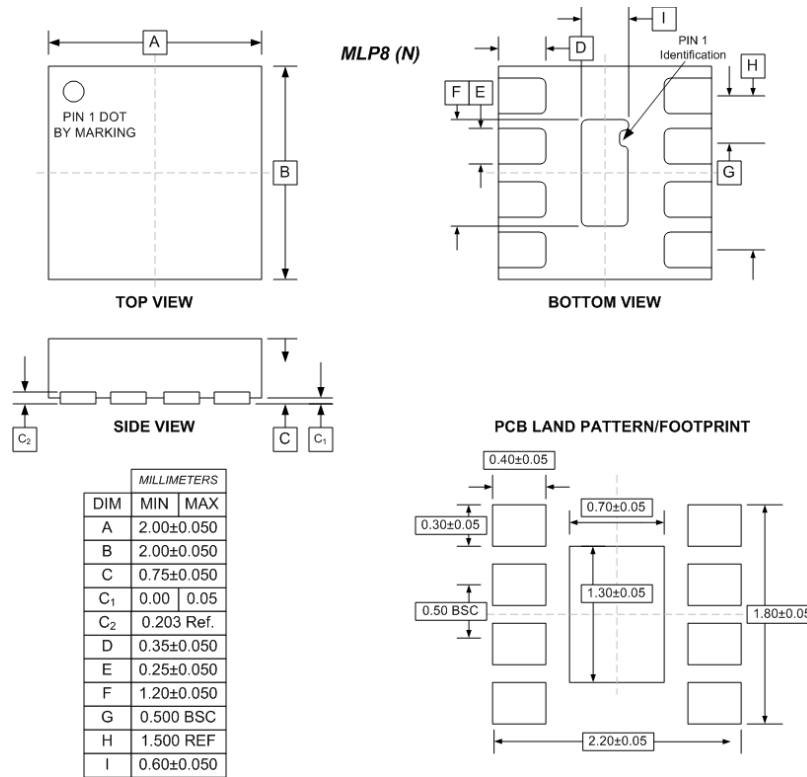
³ Duty cycle skew is the difference between a t_{PLH} and t_{PHL} propagation delay through a device.

⁴ V_{PP} is the peak-to-peak differential input swing for which AC parameters are guaranteed. The device has a voltage gain of ≈ 20 to Q/ outputs and a voltage gain of ≈ 100 to Q_{HG} outputs.

PACKAGE DIAGRAM
MLP16
Green/RoHS compliant/Pb-Free
MSL=1



PACKAGE DIAGRAM
MLP8
Green/RoHS compliant/Pb-Free
MSL=1



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